IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Priority Application Serial No
Priority Filing Date August 28, 2001
Inventor Leonard Forbes
Assignee Micron Technology, Inc.
Priority Group Art Unit
Priority Examiner Viet Q. Nguyen
Attorney's Docket No
Title: A Four Terminal Memory Cell, a Two-Transistor SRAM Cell, a SRAM
Array, a Computer System, a Process for Forming a SRAM Cell, a
Process for Turning a SRAM Cell OFF, a Process for Writing a SRAM Cell
and a Process for Reading Data from a SRAM Cell

INFORMATION DISCLOSURE STATEMENT

References -- See attached Form PTO-1449

In compliance with 37 C.F.R. §§ 1.56, 1.97, and 1.98, your attention is directed to the references which are listed on the attached Form PTO-1449. No admission is made regarding whether all the submitted references are prior art.

The listed references were cited by, or submitted to, the Office in the parent, co-pending application of the above-identified application. The above-identified application is a continuation application of co-pending application Serial No. 09/941,369, filed August 28, 2001. Such prior disclosure is sufficient for the above-identified application as far as copies of the references are concerned. 37 C.F.R. §1.98(d) and MPEP §609(2). However, copies of the new art cited with this filing are enclosed including references AK, AL, and AN.

Citation of the referenced art is respectfully requested.

Respectfully submitted,

Dated: 80

Rv.

James D. Shaurette

Reg. No. 39,833

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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.														

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